

# 2N5638

### **N-Channel Switch**

- This device is designed for low level analog switchng, sample and hold circuits and chopper stabilized amplifiers.
- Sourced from process 51.



1. Drain 2. Source 3. Gate

# Absolute Maximum Ratings \* T<sub>C</sub>=25°C unless otherwise noted

| Symbol                            | Parameter  | Value      | Units |
|-----------------------------------|--|------------|-------|
| V <sub>DG</sub>                   | Drain-Gate Voltage                               | 30         | V     |
| V <sub>GS</sub>                   | Gate-Source Voltage                              | -30        | V     |
| I <sub>GF</sub>                   | Forward Gate Current                             | 50         | mA    |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Junction Temperature Range | -55 ~ +150 | °C    |

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
  These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

| Symbol                       | Parameter                           | Test Condition   | Min. | Тур. | Max. | Units |
|------------------------------|-------------------------------------|--|------|------|------|-------|
| Off Charac                   | Off Characteristics                 |  |      |      |      |       |
| V <sub>(BR)GSS</sub>         | Gate-Source Breakdown Voltage       | $V_{DS} = 0, I_{G} = -10\mu A$ -30                     |      |      | V    |       |
| I <sub>GSS</sub>             | Gate Reverse Current                | $V_{GS} = -15V, V_{DS} = 0$                            |      |      | -1.0 | nA    |
| I <sub>D(off)</sub>          | Drain Cutoff Leakage Current        | V <sub>DS</sub> = 12V, V <sub>GS</sub> = 15V           |      |      | 1.0  | nA    |
| On Characteristics           |                                     |  |      |      |      |       |
| I <sub>DSS</sub>             | Zero-Gate Voltage Drain Current *   | V <sub>DS</sub> = 20V, I <sub>GS</sub> = 0             | 50   |      |      | mA    |
| r <sub>DS(on)</sub>          | Drain-Source On Resistance          | V <sub>GS</sub> = 0V, I <sub>D</sub> = 1.0mA           |      |      | 30   | Ω     |
| Small Signal Characteristics |                                     |  |      |      |      |       |
| r <sub>ds(on)</sub>          | Drain-Source On Resistance          | $V_{DS} = V_{GS} = 0, f = 1.0 \text{kHz}$              |      |      | 30   | Ω     |
| C <sub>iss</sub>             | Input Capacitance                   | V <sub>DS</sub> = 0, V <sub>GS</sub> = 12V, f = 1.0MHz |      |      | 10   | pF    |
| C <sub>rss</sub>             | Reverse Transfer Capacitance        | $V_{DS} = 0V, V_{GS} = 12V, f = 1.0MHz$                |      |      | 4.0  | pF    |
| Switching                    | Characteristics                     |  |      |      |      |       |
| t <sub>d(on)</sub>           | Trun On Delay Time                  | $V_{DD} = 10V, V_{GS(on)} = 0$                         |      |      | 4.0  | ns    |
| t <sub>r</sub>               | Rise Time                           | $V_{GS(off)} = -12, I_{D(on)} = 12mA$                  |      |      | 5.0  | ns    |
| t <sub>d(off)</sub>          | Trun Off Delay Time                 | $R_{G} = 50\Omega$                                     |      |      | 5.0  | ns    |
| t <sub>f</sub>               | Fall Time                           |  |      |      | 10   | ns    |
| Pulco Toet: Pu               | Ise Width < 300us Duty Cycle < 1.0% | ·  |      |      |      |       |

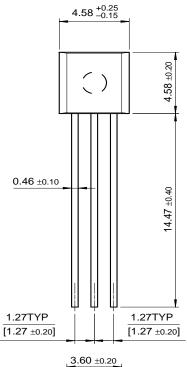
Pulse Test: Pulse Width  $\leq 300 \mu s, \, Duty \, Cycle \leq 1.0\%$ 

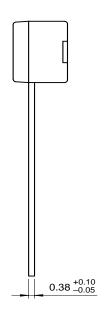
# Thermal Characteristics T<sub>A</sub>=25°C unless otherwise noted

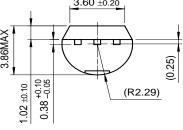
| Symbol          | Parameter                               | Max. | Units |
|-----------------|---|------|-------|
| P <sub>D</sub>  | Total Device Dissipation                | 350  | mW    |
| _               | Derate above 25°C                       | 2.8  | mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    | 125  | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 357  | °C/W  |

# **Package Dimensions**

TO-92







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|--------------------------|---------------------------|---|
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